GI1386

PNP EPITAXIAL SILICON TRANSISTOR

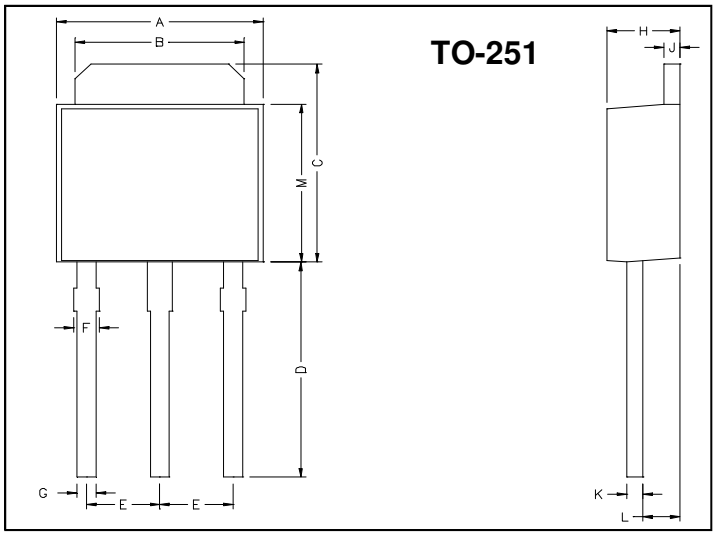
Description

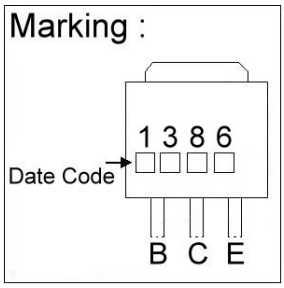
The GI1386 is designed for low frequency applications.

Features

- Low V_{CE}(sat) =-0.55V(Typ.) (I_C/I_B=-4A/-0.1A)
- Excellent DC current gain characteristics

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	7.20	7.80	K	0.45	0.60
E	2.30 REF.		L	0.90	1.50
F	0.60	0.90	M	5.40	5.80

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-5	A
*Collector Current (Pulse)	I_C	-10	A
Total Power Dissipation (T_C=25℃)	P_D	20	W

Electrical Characteristics (Ta = 25℃)

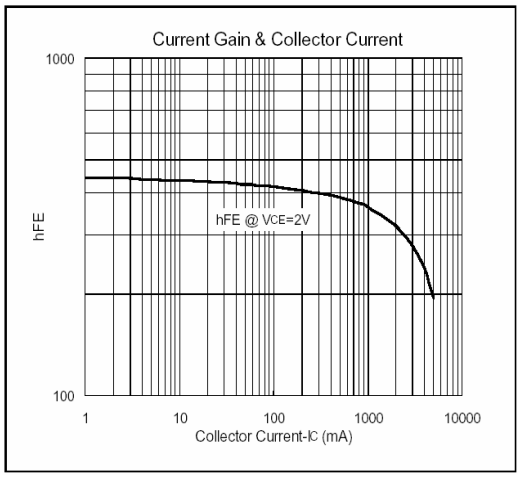
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-30	-	-	V	I_C=-50uA , I_E=0
BV_{CEO}	-20	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-6	-	-	V	I_E=-50uA ,I_C=0
I_{CBO}	-	-	-500	nA	V_{CB}=-20V, I_E=0
I_{EBO}	-	-	-500	nA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)}$	-	-	-1	V	I_C=-4A, I_B=-0.1A
*h_{FE}	82	-	580		V_{CE}=-2V, I_C=-0.5A
fT	-	120	-	MHz	V_{CE}=-6V, I_E=50mA, f=30MHz
Cob	-	60	-	pF	V_{CB}=-20V, I_E=0, f=1MHz

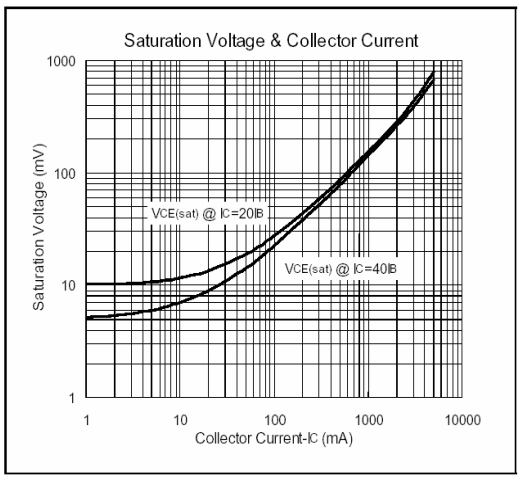
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

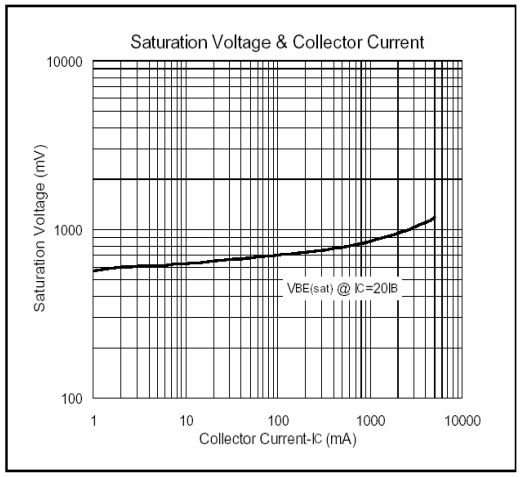
Classification Of h_{FE}

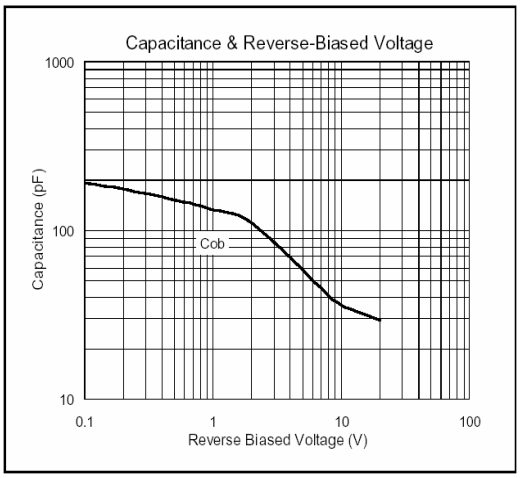
Rank	P	Q	R	E
Range	82 - 180	120 - 270	180 - 390	370 - 580

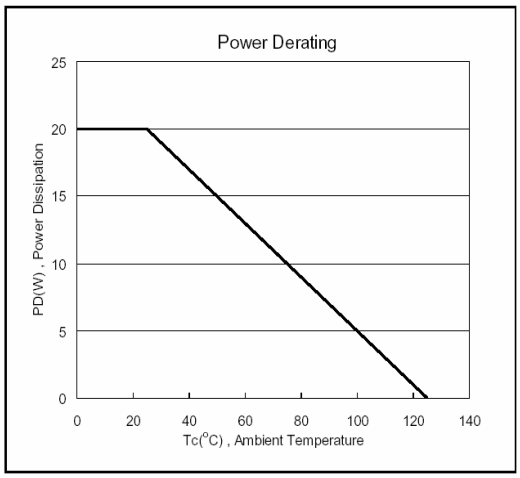
Characteristics Curve

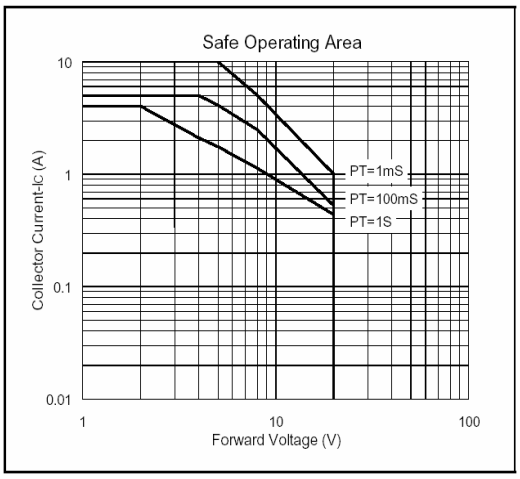












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